

**IN THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-20. (Canceled)

21. (Currently Amended) A method for manufacturing a thin film transistor, comprising the steps of:

forming a first insulating film having a depression and a projection;

forming a first conductive film in the depression by spurling droplets containing a first conductive material;

forming a second insulating film so as to cover the first insulating film and the first conductive film;

forming a first semiconductor film over the second insulating film; [[and]]

forming a second semiconductor film containing an impurity element over the first semiconductor film;

simultaneously patterning the second insulating film, the first semiconductor film and the second semiconductor film,

forming a second conductive film by spurling droplets containing a second conductive material so that the second conductive film covers a side surface of each of the second insulating film, the first semiconductor film and the second semiconductor film;

etching the second semiconductor film by using the second conductive film as a mask;

wherein the first insulating film and the first conductive film are formed so that [[the]] top surfaces thereof are flat.

22-23. (Canceled)

24. (Withdrawn – Currently Amended) A method for manufacturing a thin film transistor according to ~~any one of Claims 20 to 22~~ claim 21,

wherein a composition containing an insulating material is spurlted and a composition containing [[a]] the first conductive material is simultaneously spurlted, whereby forming the first insulating film having the depression and the projection, and whereby forming [[a]] the first conductive film in the depression.

25. (Withdrawn – Currently Amended) A method for manufacturing a thin film transistor according to ~~any one of Claims 20 to 22~~ claim 21,

wherein the first insulating film having the depression and the projection is formed by spurtng a composition containing an insulating material,~~and~~  
~~the conductive film is formed by spurtng a composition containing a conductive material into the depression.~~

26. (Withdrawn – Currently Amended) A method for manufacturing a thin film transistor according to Claim 25,

wherein the first insulating film having the depression and the projection is formed by spurtng a composition containing an insulating material,

the first insulating film is heated, and

the first conductive ~~material~~ film is formed by spurtng a composition containing a conductive material into the depression.

27. (Withdrawn – Currently Amended) A method for manufacturing a thin film transistor according to ~~any one of Claims 20 to 22 and 28–30~~ claim 21,

wherein an insulating film is formed over a channel region of the first semiconductor film.

28-30. (Canceled)

31. (Withdrawn – Currently Amended) A method for manufacturing a thin film transistor according to ~~any one of Claims 20 to 22 and 28–30~~ claim 21,

wherein the first insulating film having the depression and the projection is formed so that the width of the depression is 5  $\mu\text{m}$  to 100  $\mu\text{m}$ , and the depth of the depression is 1  $\mu\text{m}$  to 10  $\mu\text{m}$ .

32 (Withdrawn – Currently Amended) A method for manufacturing a thin film transistor according to ~~any one of Claims 28 to 30~~ claim 31,

wherein the first insulating film having the depression and the projection formed in a region where ~~[[the]]~~ a source electrode and ~~[[the]]~~ a drain electrode are to be formed so that

the width of the depression is 5  $\mu\text{m}$  to 20  $\mu\text{m}$ , and the depth of the depression is 1.5  $\mu\text{m}$  to 2.5  $\mu\text{m}$ .

33. (Canceled)

34. (Withdrawn – Currently Amended) A method for manufacturing a thin film transistor according to ~~any one of Claims 20 to 22 and 28-30~~ claim 21,

wherein an amount of the droplets containing [[a]] the first conductive material to be spurted is 0.1 pl to 40 pl.

35-66. (Canceled)

67. (New) A method for manufacturing a thin film transistor, comprising the steps of:  
forming a first insulating film having a depression and a projection;

forming a first conductive film in the depression by spurling droplets containing a first conductive material and a solvent;

baking the first conductive film in an oxygen containing atmosphere;

forming a second insulating film so as to cover the first insulating film and the first conductive film;

forming a first semiconductor film over the second insulating film;

forming a second semiconductor film containing an impurity element over the first semiconductor film;

simultaneously patterning the second insulating film, the first semiconductor film and the second semiconductor film,

forming a second conductive film by spurling droplets containing a second conductive material so that the second conductive film covers a side surface of each of the second insulating film, the first semiconductor film and the second semiconductor film;

etching the second semiconductor film by using the second conductive film as a mask;

wherein the first insulating film and the first conductive film are formed so that top surfaces thereof are flat.

68. (New) A method for manufacturing a thin film transistor, comprising the steps of:  
forming a first insulating film having a depression and a projection;  
forming a first conductive film in the depression by spurting droplets containing a first conductive material;  
forming a second insulating film so as to cover the first insulating film and the first conductive film;  
forming a first semiconductor film over the second insulating film;  
forming a second semiconductor film containing an impurity element over the first semiconductor film;  
simultaneously patterning the second insulating film, the first semiconductor film and the second semiconductor film,  
forming a second conductive film by spurting droplets containing a second conductive material so that the second conductive film covers a side surface of each of the second insulating film, the first semiconductor film and the second semiconductor film;  
etching the second semiconductor film by using the second conductive film as a mask;  
wherein the first insulating film and the first conductive film are formed so that top surfaces thereof are flat, and  
wherein the second insulating film, the first semiconductor film and the second semiconductor film are formed consecutively without being exposed to the atmosphere.
69. (New) A method for manufacturing a thin film transistor according to claim 67,  
wherein a composition containing an insulating material is spurted and a composition containing the first conductive material is simultaneously spurted, whereby forming the first insulating film having the depression and the projection, and whereby forming the first conductive film in the depression.
70. (New) A method for manufacturing a thin film transistor according to claim 67,  
wherein the first insulating film having the depression and the projection is formed by spurting a composition containing an insulating material.
71. (New) A method for manufacturing a thin film transistor according to claim 70,  
wherein the first insulating film having the depression and the projection is formed by spurting a composition containing an insulating material,

the first insulating film is heated, and  
the first conductive film is formed by spurring a composition containing a conductive material into the depression.

72. (New) A method for manufacturing a thin film transistor according to claim 67, wherein an insulating film is formed over a channel region of the first semiconductor film.

73. (New) A method for manufacturing a thin film transistor according to claim 67, wherein the first insulating film having the depression and the projection is formed so that the width of the depression is 5  $\mu\text{m}$  to 100  $\mu\text{m}$ , and the depth of the depression is 1  $\mu\text{m}$  to 10  $\mu\text{m}$ .

74. (New) A method for manufacturing a thin film transistor according to claim 73, wherein the first insulating film having the depression and the projection formed in a region where a source electrode and a drain electrode are to be formed so that the width of the depression is 5  $\mu\text{m}$  to 20  $\mu\text{m}$ , and the depth of the depression is 1.5  $\mu\text{m}$  to 2.5  $\mu\text{m}$ .

75. (New) A method for manufacturing a thin film transistor according to claim 67, wherein an amount of the droplets containing the first conductive material to be spurted is 0.1 pl to 40 pl.

76. (New) A method for manufacturing a thin film transistor according to claim 68, wherein a composition containing an insulating material is spurted and a composition containing the first conductive material is simultaneously spurted, whereby forming the first insulating film having the depression and the projection, and whereby forming the first conductive film in the depression.

77. (New) A method for manufacturing a thin film transistor according to claim 68, wherein the first insulating film having the depression and the projection is formed by spurring a composition containing an insulating material.

78. (New) A method for manufacturing a thin film transistor according to claim 77,  
wherein the first insulating film having the depression and the projection is formed by  
spurting a composition containing an insulating material,  
the first insulating film is heated, and  
the first conductive film is formed by spurting a composition containing a conductive  
material into the depression.
79. (New) A method for manufacturing a thin film transistor according to claim 68,  
wherein an insulating film is formed over a channel region of the first semiconductor  
film.
80. (New) A method for manufacturing a thin film transistor according to claim 68,  
wherein the first insulating film having the depression and the projection is formed so  
that the width of the depression is 5  $\mu\text{m}$  to 100  $\mu\text{m}$ , and the depth of the depression is 1  $\mu\text{m}$  to  
10  $\mu\text{m}$ .
81. (New) A method for manufacturing a thin film transistor according to claim 80,  
wherein the first insulating film having the depression and the projection formed in a  
region where a source electrode and a drain electrode are to be formed so that the width of the  
depression is 5  $\mu\text{m}$  to 20  $\mu\text{m}$ , and the depth of the depression is 1.5  $\mu\text{m}$  to 2.5  $\mu\text{m}$ .
82. (New) A method for manufacturing a thin film transistor according to claim 68,  
wherein an amount of the droplets containing the first conductive material to be  
spurted is 0.1 pl to 40 pl.